

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> T <sub>C</sub> = +25°C
100V	14.5mΩ @ V <sub>GS</sub> = 10V	56A
	19.5mΩ @ V <sub>GS</sub> = 6V	49A

## Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is AEC-Q101 qualified, supported by a PPAP, and is ideal for use in:

- Motor controls
- DC-DC converters
- Power management

## Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- Thermally Efficient Package – Cooler Running Applications
- Low R<sub>DS(ON)</sub> – Minimizes On-State Losses
- Low Input Capacitance
- Fast Switching Speed
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen- and Antimony-Free. “Green” Device (Note 3)**
- **The DIODES™ DMTH10H015SPSQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

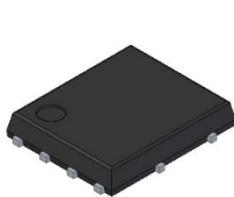
<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

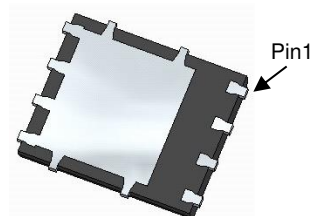
- Package: PowerDI<sup>®</sup>5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Lead-Frame. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

Site 1:

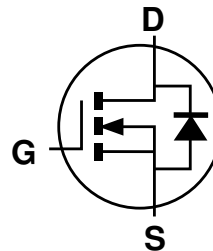
PowerDI5060-8



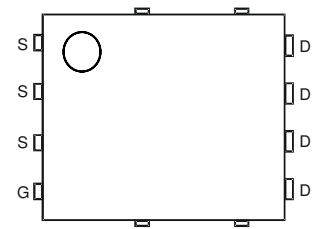
Top View



Bottom View



Internal Schematic



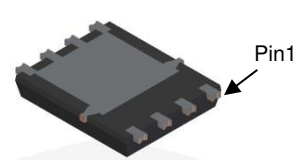
Top View  
Pin Configuration

Site 2:

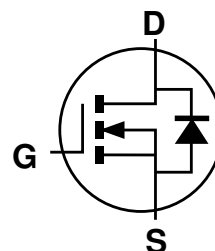
PowerDI5060-8 (SWP) (Type UX)



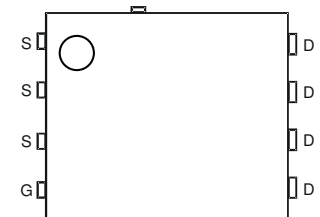
Top View



Bottom View



Internal Schematic



Top View  
Pin Configuration

Notes:

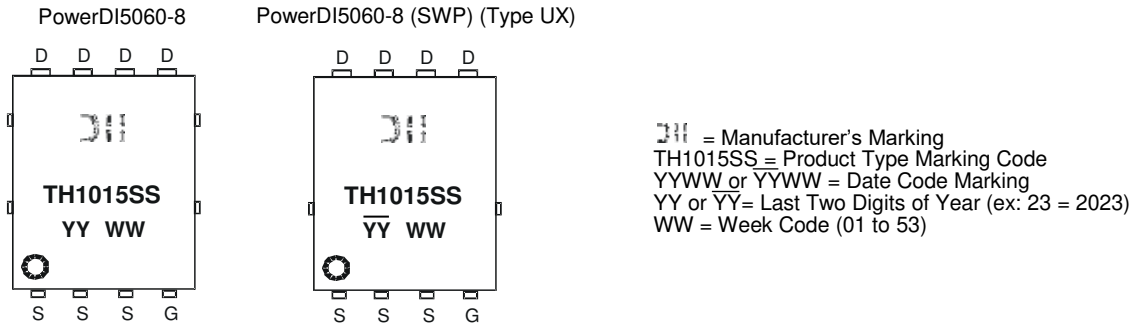
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

### Ordering Information (Note 4)

Part Number	Package	Packing	
		Qty.	Carrier
DMTH10H015SPSQ-13	PowerDI5060-8	2,500	Tape & Reel
DMTH10H015SPSQ-13	PowerDI5060-8 (SWP) (Type UX)	2,500	Tape & Reel

Notes: 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

### Marking Information



### Maximum Ratings (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	100	V	
Gate-Source Voltage	V <sub>GSS</sub>	±20	V	
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	I <sub>D</sub>	Steady State	56	A
		T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	39	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	120	A	
Maximum Continuous Body Diode Forward Current (Note 5)	I <sub>S</sub>	56	A	
Avalanche Current L = 3mH	I <sub>AS</sub>	7.5	A	
Avalanche Energy L = 3mH	E <sub>AS</sub>	85	mJ	
Avalanche Current, L = 0.1mH	I <sub>AS</sub>	15.8	A	
Avalanche Energy, L = 0.1mH	E <sub>AS</sub>	12.5	mJ	

### Thermal Characteristics

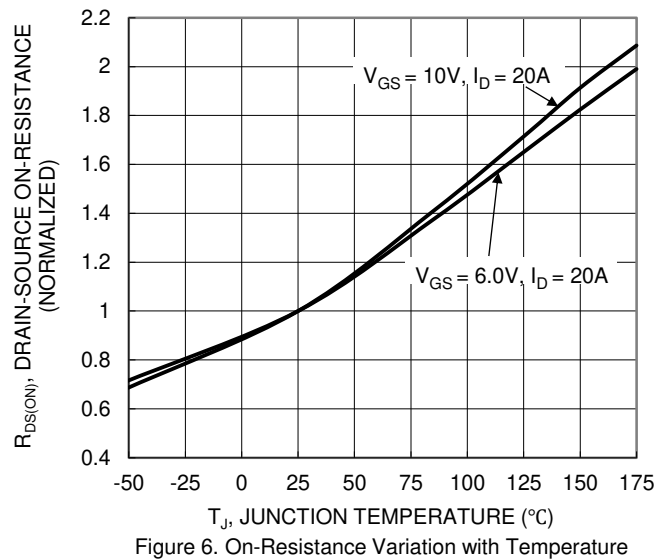
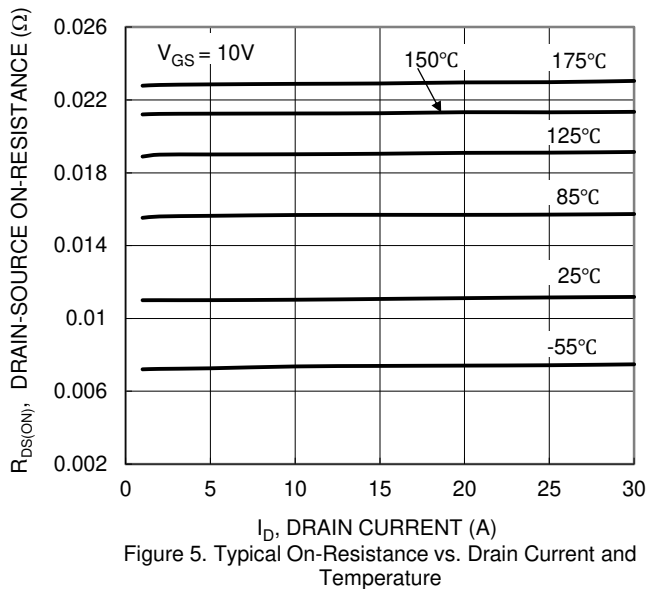
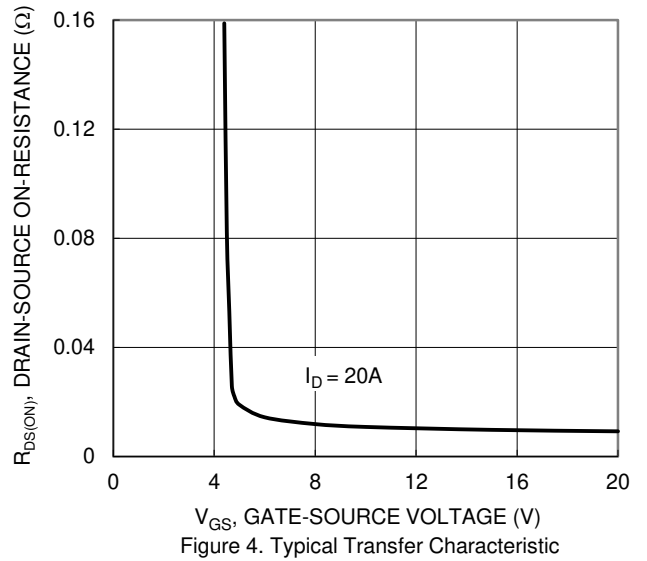
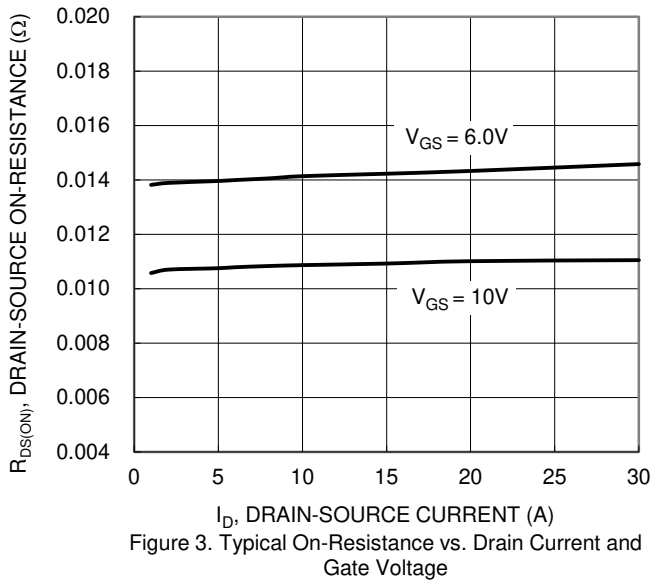
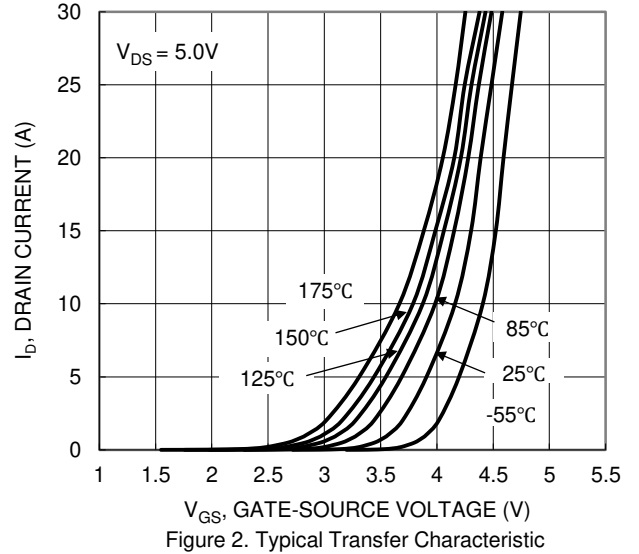
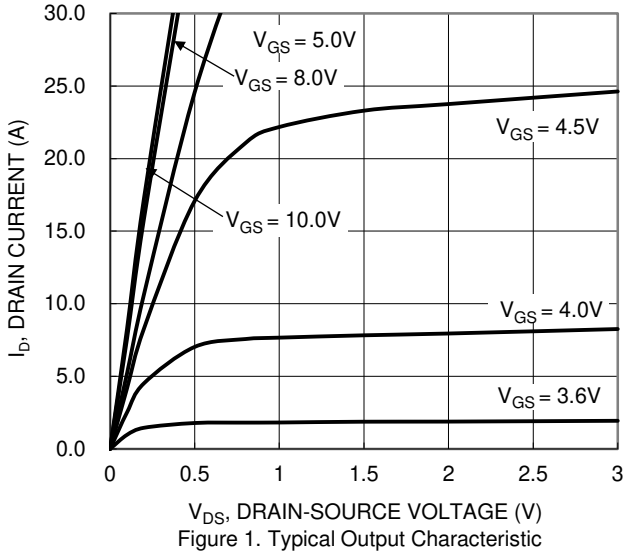
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6) T <sub>A</sub> = +25°C	P <sub>D</sub>	2.7	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	55	°C/W
Total Power Dissipation (Note 5) T <sub>C</sub> = +25°C	P <sub>D</sub>	94	W
Thermal Resistance, Junction to Case (Note 5)	R <sub>θJC</sub>	1.6	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +175	°C

Notes: 5. Thermal resistance from junction to soldering point (on the exposed drain pad).  
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

### Electrical Characteristics (@ T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS</b> (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 1mA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	—	—	1	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS</b> (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	2	—	4	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	11.3	14.5	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
		—	14.7	19.5		V <sub>GS</sub> = 6V, I <sub>D</sub> = 20A
Diode Forward Voltage	V <sub>SD</sub>	—	0.9	1.3	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 20A
<b>DYNAMIC CHARACTERISTICS</b> (Note 8)						
Input Capacitance	C <sub>iss</sub>	—	2343	—	pF	V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V f = 1MHz
Output Capacitance	C <sub>oss</sub>	—	487	—		
Reverse Transfer Capacitance	C <sub>rss</sub>	—	26	—		
Gate Resistance	R <sub>G</sub>	—	0.69	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>G</sub>	—	30.1	—	nC	V <sub>DD</sub> = 50V, I <sub>D</sub> = 10A, V <sub>GS</sub> = 10V
Gate-Source Charge	Q <sub>GS</sub>	—	7.5	—		
Gate-Drain Charge	Q <sub>GD</sub>	—	6.5	—		
Turn-On Delay Time	t <sub>D(ON)</sub>	—	9.8	—	ns	V <sub>DD</sub> = 50V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A, R <sub>G</sub> = 6Ω
Turn-On Rise Time	t <sub>R</sub>	—	7.8	—		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	22.5	—		
Turn-Off Fall Time	t <sub>F</sub>	—	9.6	—		
Reverse Recovery Time	t <sub>RR</sub>	—	43.1	—	ns	I <sub>F</sub> = 10A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	—	65.1	—	nC	

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.



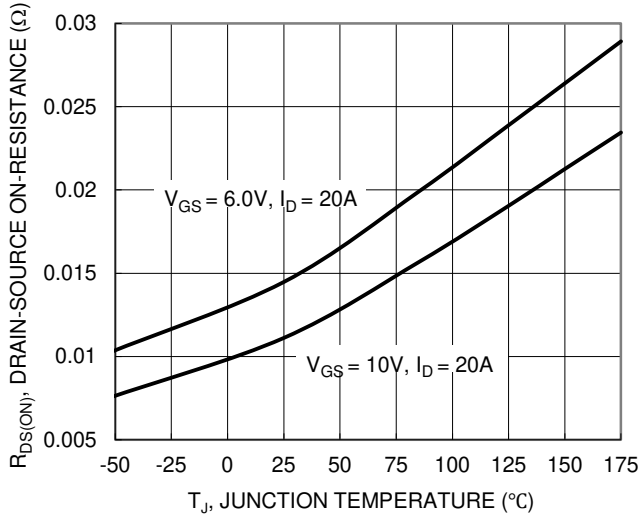


Figure 7. On-Resistance Variation with Temperature

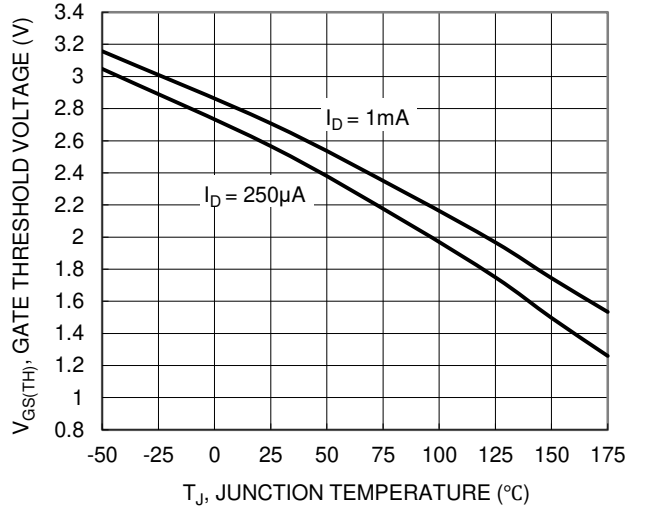


Figure 8. Gate Threshold Variation vs. Junction Temperature

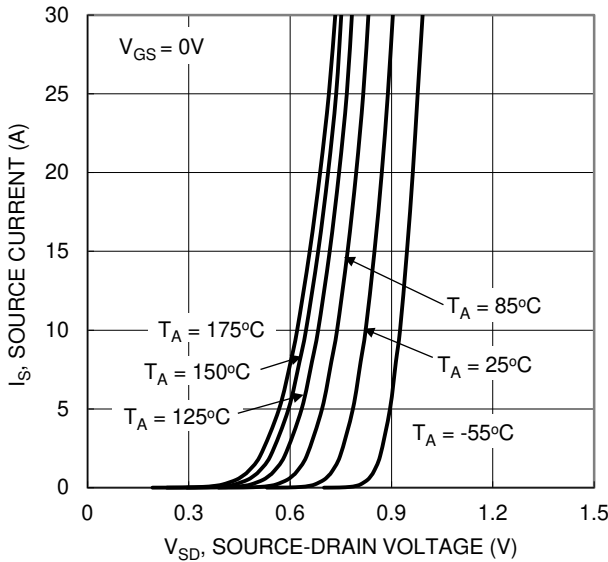


Figure 9. Diode Forward Voltage vs. Current

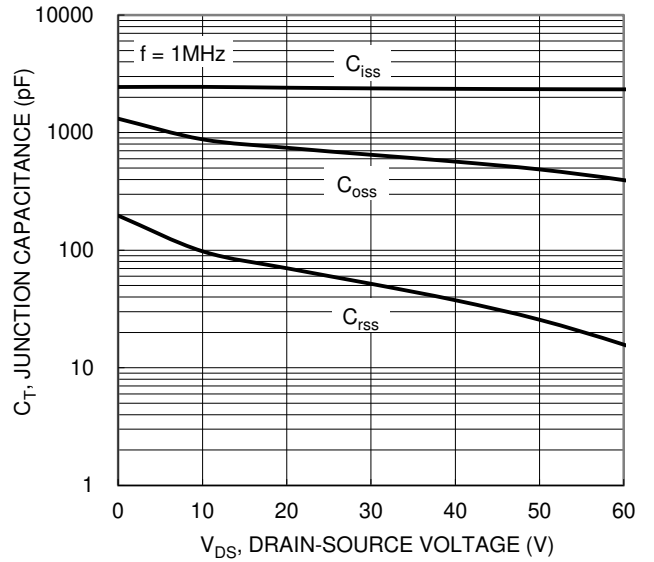


Figure 10. Typical Junction Capacitance

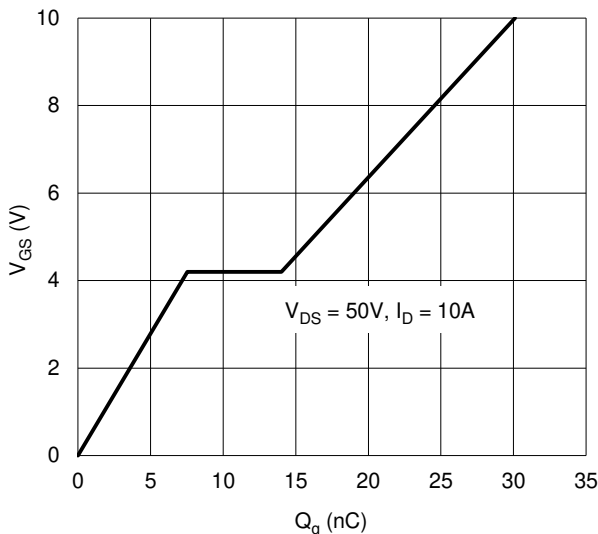


Figure 11. Gate Charge

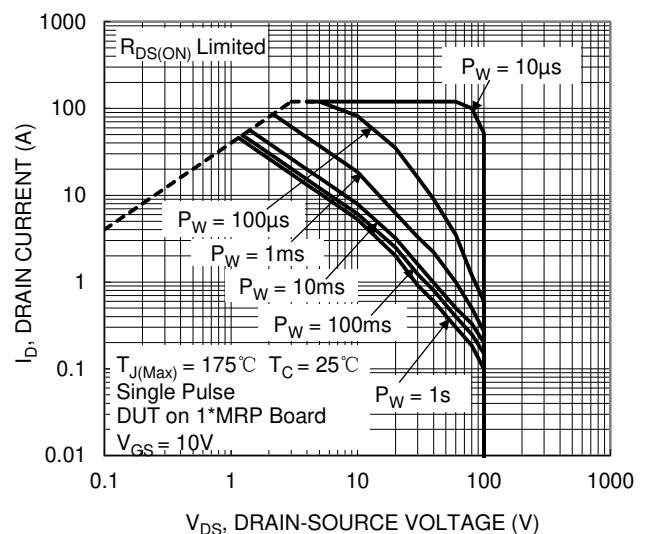


Figure 12. SOA, Safe Operation Area

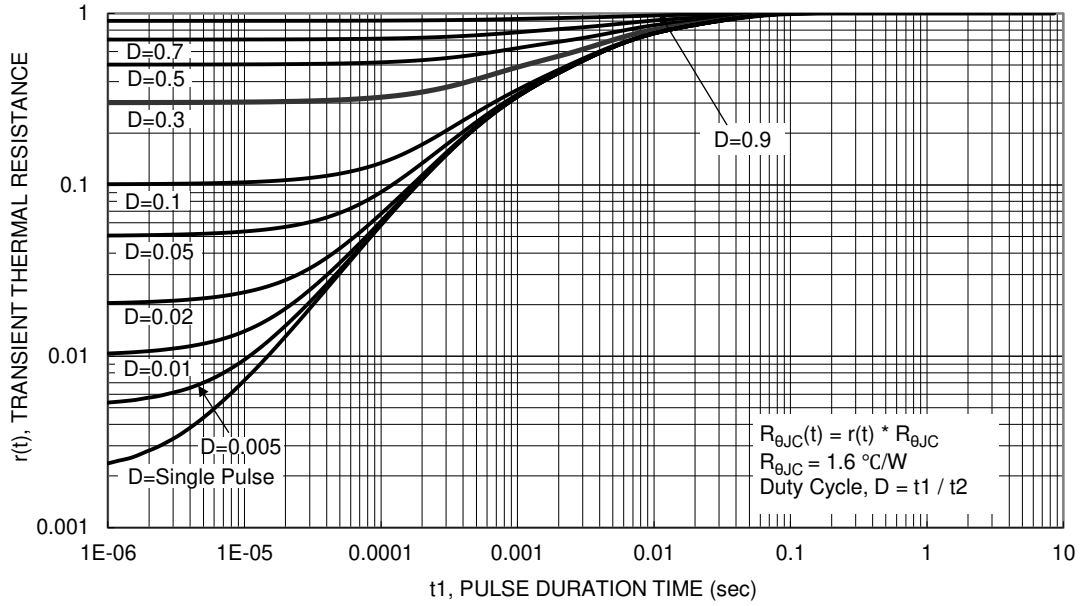


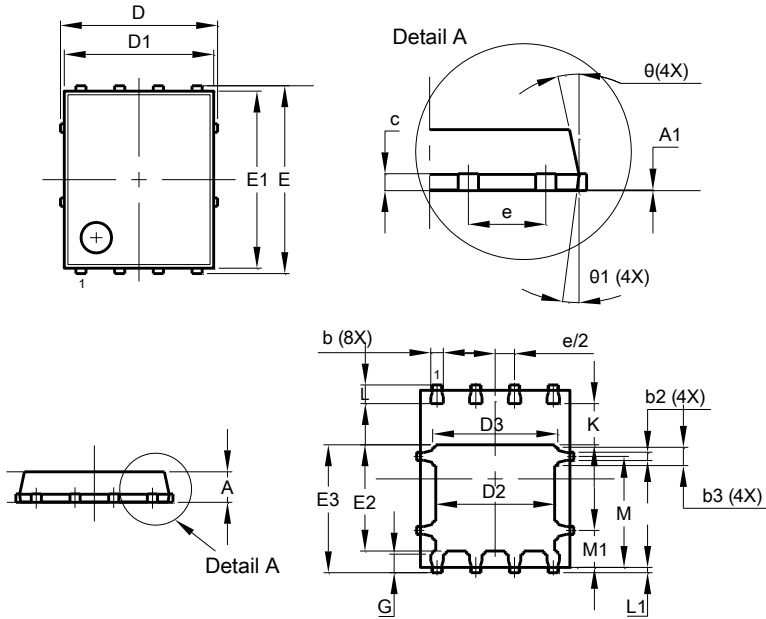
Figure 13. Transient Thermal Resistance

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

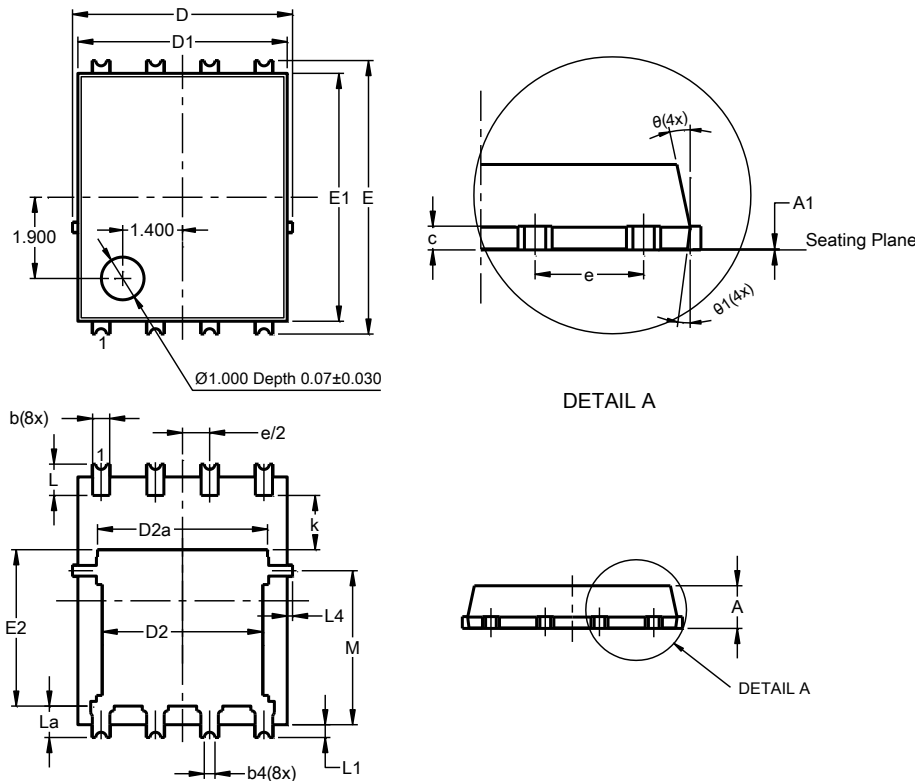
**PowerDI5060-8**



PowerDI5060-8			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0.00	0.05	-
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	-	-
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
θ	10°	12°	11°
θ1	6°	8°	7°
<b>All Dimensions in mm</b>			

Site 2:

**PowerDI5060-8 (SWP) (Type UX)**



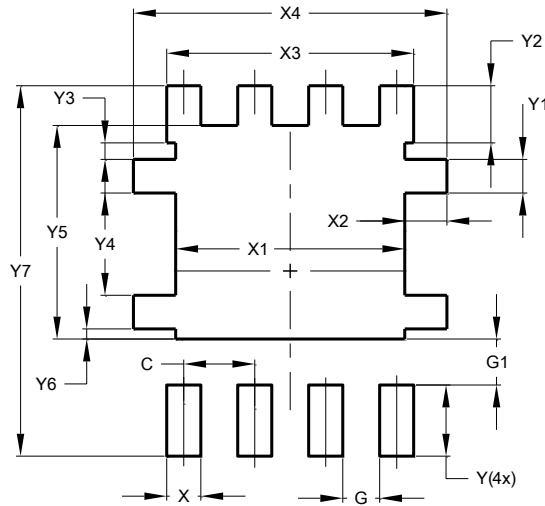
PowerDI5060-8 (SWP) (Type UX)			
Dim	Min	Max	Typ
A	0.90	1.10	1.00
A1	0	0.05	--
b	0.30	0.50	0.41
b2	0.20	0.35	0.25
b4	0.25REF		
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.56	3.96	3.76
D2a	3.78	4.18	3.98
E	6.40 BSC		
E1	5.60	6.00	5.80
E2	3.46	3.86	3.66
E2a	4.195	4.595	4.395
e	1.27BSC		
k	1.05	--	--
L	0.635	0.835	0.735
La	0.635	0.835	0.735
L1	0.200	0.400	0.300
L1a	0.050REF		
L4	0.025	0.225	0.125
M	3.205	4.005	3.605
θ	10°	12°	11°
θ1	6°	8°	7°
<b>All Dimensions in mm</b>			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

Site 1:

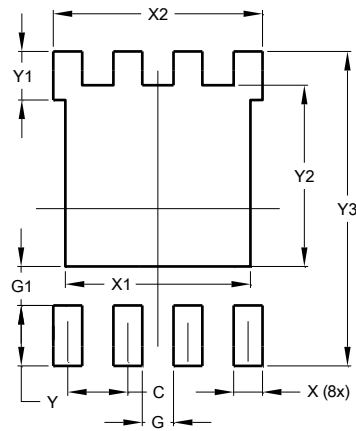
**PowerDI5060-8**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

Site 2:

**PowerDI5060-8 (SWP) (Type UX)**



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	4.420
Y	1.270
Y1	1.020
Y2	3.810
Y3	6.610



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